Document Title

512K x 16 bit Super Low Power and Low Voltage Full CMOS RAM

Revision History

Revision No.	History	Draft date	Remark
0.0	Initial Draft	Jul. 04th, 2006	Final
0.1	Corrected timing diagrams & functions (about CS2)	Aug. 16th, 2006	Final
0.2	Removed 60ns part	Aug. 21st, 2006	Final
0.3	Added Power Up Sequence	Sep. 6th, 2006	Final
0.4	Removed VCCQ related information & typo.	Dec. 15th, 2006	Final
0.5	Added “RoHS compliant” descriptions	Apr. 06th, 2007	Final

512K x 16 bit Super Low Power and Low Voltage Full CMOS RAM

FEATURES

- Process Technology : Full CMOS
- Organization : 512K x 16
- Power Supply Voltage : 2.7~3.6V
- Three state output and TTL Compatible
- Package Type : 44-TSOPII (400F)
- Automatic power-down when deselected
- **CMP0817BA0-P70I is RoHS Compliant**

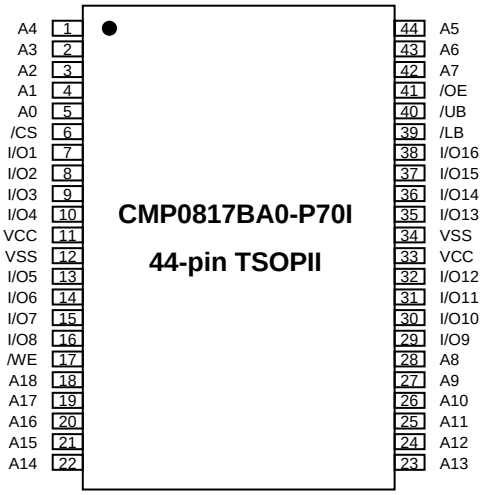
PRODUCT FAMILY

Product Family	Operating Temperature	Operating Voltage (V)			Speed	Power Dissipation					
						ICC1		ICC2		ISB1 (CMOS Standby Current)	
						f = 1MHz		f = fmax			
		Min.	Typ.	Max.		Typ.	Max.	Typ.	Max.	Typ.	Max.
CMP0817BA0-P70I	Industrial (-40~85'C)	2.7	3.0	3.6	70ns	1.5mA	3mA	12mA	20mA	30uA	70uA

1. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at Vcc = Vcc (typ) and T_A = 25C.

2. . T=TSOP, P=TSOP (Pb-Free), W=WAFER

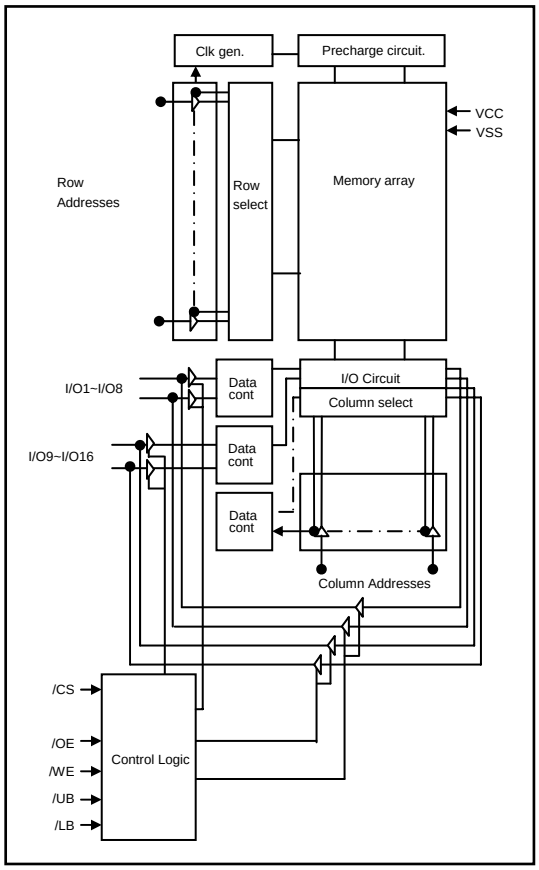
PIN DESCRIPTION



44-Pin TSOP-II : Top View

Name	Function	Name	Function
/CS	Chip Select Input	VCC	Core Power
/OE	Output Enable Input		
/WE	Write Enable Input	VSS	Ground
A0~A18	Address Inputs	/UB	Upper Byte(I/O9~16)
I/O1~I/O16	Data Inputs/Outputs	/LB	Lower Byte(I/O 1~8)
NC	No Connection		

FUNCTIONAL BLOCK DIAGRAM



PRODUCT LIST

Industrial Temperature Products(-40~85'C)	
Part Name	**Function**
CMP0817BA0-P70I	44-TSOPII, 70ns, VCC=3.0V

1. T=TSOP, P=TSOP (Pb-Free), W=WAFER

FUNCTIONAL DESCRIPTION

/CS	/OE	/WE	/LB	/UB	I/O1-8	I/O9-16	Mode	Power
H	X[1)]	X[1)]	X[1)]	X[1)]	High-Z	High-Z	Deselect/Power-down	Standby
X[1)]	X[1)]	X[1)]	H	H	High-Z	High-Z	Deselect/Power-down	Standby
L	H	H	L	X[1)]	High-Z	High-Z	Output Disabled	Active
	H	H	X[1)]	L	High-Z	High-Z	Output Disabled	Active
L	L	H	L	H	Dout	High-Z	Lower Byte Read	Active
			H	L	High-Z	Dout	Upper Byte Read	Active
			L	L	Dout	Dout	Word Read	Active
	X[1)]	L	L	H	Din	High-Z	Lower Byte Write	Active
			H	L	High-Z	Din	Upper Byte Write	Active
			L	L	Din	Din	Word Write	Active

1. X means don't care.(Must be low or high state)

ABSOLUTE MAXIMUM RATINGS[1)]

Item	Symbol	Ratings	Unit
Voltage on any pin relative to Vss	V_{IN}, V_{OUT}	-0.2 to Vcc+0.3V	V
Voltage on Vcc supply relative to Vss	V_{CC}	-0.2 to 3.6	V
Power Dissipation	P_D	1.0	W
Storage temperature	T_{STG}	-65 to 150	'C
Operating Temperature	T_A	-40 to 85	'C

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for Industrial periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS[1)]

Item	Symbol	CMP0817BA0		Unit
		Min	Max	
Supply voltage	V_{CC}	2.7	3.6	V
Ground	V_{SS}	0	0	V
Input high voltage	V_{IH}	0.8VCC	VCC+0.2[2)]	V
Input low voltage	V_{IL}	-0.2[3)]	0.2VCC	V

Note :
1.T_A=-40 to 85'C, otherwise specified.
2. Overshoot : Vcc+1.0V in case of pulse width≤20ns.
3. Undershoot : -1.0V in case of pulse width≤20ns.
4. Overshoot and undershoot are sampled, not 100% tested.

CAPACITANCE[1)] (f=1MHz , T_A=25'C)

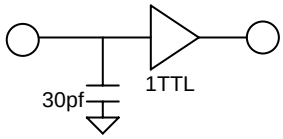
Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C_{IN}	V_{IN}=0V	-	8	pF
Input/Output capacitance	C_{IO}	V_{IO}=0V	-	8	pF

1. Capacitance is sampled, not 100% tested.

DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions	Min	Typ	Max	Unit
Input leakage current	I_{LI}	V_{IN}=V_{SS} to V_{CC}	-1	-	1	uA
Output leakage current	I_{LO}	/CS=V_{IH}, /OE=V_{IH} or /WE=V_{IL}, V_{IO}=V_{SS} to V_{CC}	-1	-	1	uA
Average operating current	I_{CC1}	Cycle time=1us, 100%duty, I_{IO}=0mA, /CS≤0.2V, V_{IN}≤0.2V or V_{IN}≥V_{CC}-0.2V	-	1.5	**3**	mA
	I_{CC2}	Cycle time=Min, I_{IO}=0mA, 100% duty, /CS=V_{IL}, V_{IN}=V_{IL} or V_{IH}	-	15	25	mA
Output low voltage	V_{OL}	I_{OL}=0.5mA			0.2VCC	V
Output high voltage	V_{OH}	I_{OH}=-0.5mA	0.8VCC			V
Standby Current(TTL)	I_{SB}	/CS=V_{IH}, Other inputs=V_{IH} or V_{IL}	-	-	0.3	mA
Standby Current(CMOS)	I_{SB1}	/CS≥V_{CC}-0.2V, Other inputs=0~V_{CC}	-	-	70	uA

AC OPERATING CONDITIONS



TEST CONDITIONS(Test Load and Input/Output Reference)

Input pulse level : 0.2 to VCC-0.2V
Input rising and falling time : 5ns
Input and output reference voltage : 0.5*VCC
Output load(see right) : C_L=30pF+1TTL

AC CHARACTERISTICS(V_{CC}=2.7V~3.6V, Industrial product : T_A=-40 to 85'C)

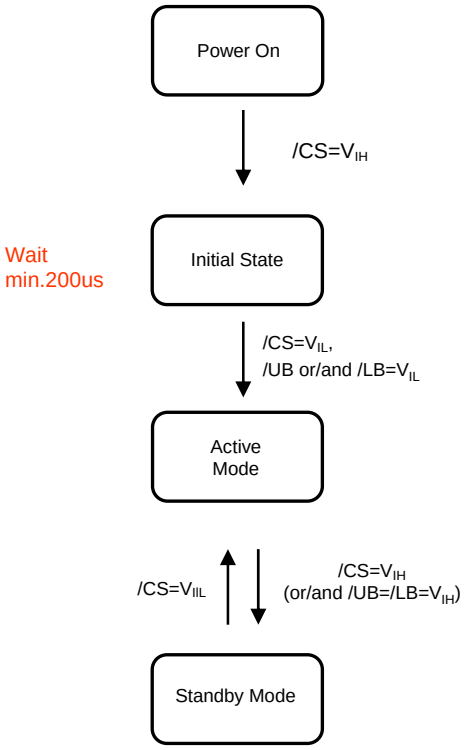
Parameter List		Symbol	70ns		Units
			Min	Max	
Read	Read Cycle Time	tRC	70	80k	ns
	Address Access Time	tAA	-	70	ns
	Chip Select to Output	tCO	-	70	ns
	Output Enable to Valid Output	tOE	-	25	ns
	/UB, /LB Access Time	tBA	-	70	ns
	Chip Select to Low-Z Output	tLZ	10	-	ns
	/UB, /LB Enable to Low-Z Output	tBLZ	10	-	ns
	Output Enable to Low-Z Output	tOLZ	5	-	ns
	Chip Disable to High- Z Output	tHZ	0	5	ns
	/UB, /LB Disable to High- Z Output	tBHZ	0	5	ns
	Output Disable to High- Z Output	tOHZ	0	5	ns
	Output Hold from Address Change	tOH	5	-	ns
Write	Write Cycle Time	tWC	70	80k	ns
	Chip Select to End of Write	tCW	60	-	ns
	Address Set-up Time	tAS	0	-	ns
	Address Valid to End of Write	tAW	60	-	ns
	/UB, /LB Valid to End of Write	tBW	60	-	ns
	Write Pulse Width	tWP	50	-	ns
	Write Recovery Time	tWR	0	-	ns
	Write to Output High-Z	tWHZ	0	5	ns
	Data to Write Time Overlap	tDW	20	-	ns
	Data Hold from Write Time	tDH	0	-	ns
	End Write to Output Low-Z	tOW	5	-	ns
/CS High Pulse Width[1)]		tCP	10	-	ns

1. /CS High Pulse Width is defined by /CS or (/UB and /LB) because /UB & /LB can make standby mode when /UB=High and /LB=High.

Power Up Sequence

1. Apply Power
2. Maintain stable power for a minimum of 200us with /CS=VIH

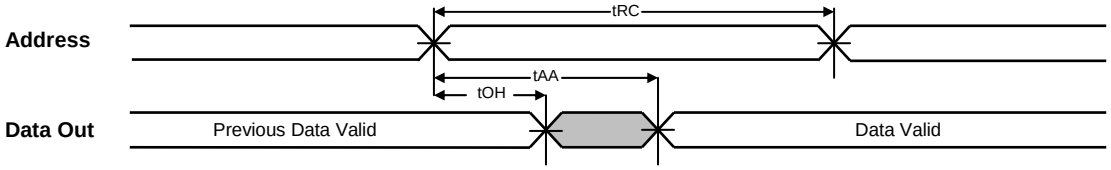
Standby Mode State machines



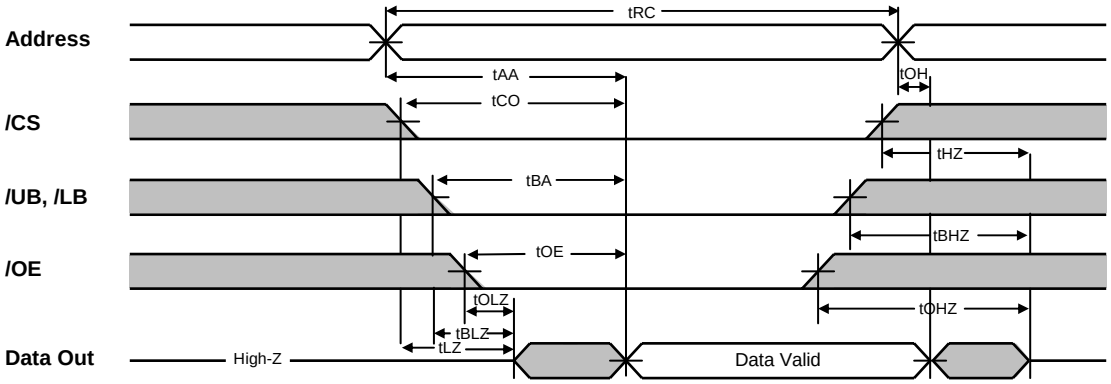
Standby Mode Characteristics

Mode	Memory Cell Data	Standby Current(uA)	Wait Time(us)
Standby	Valid	70 (ISB1)	0

READ CYCLE (1) (Address controlled,/CS=/OE=VIL, /UB or/and /LB=VIL)

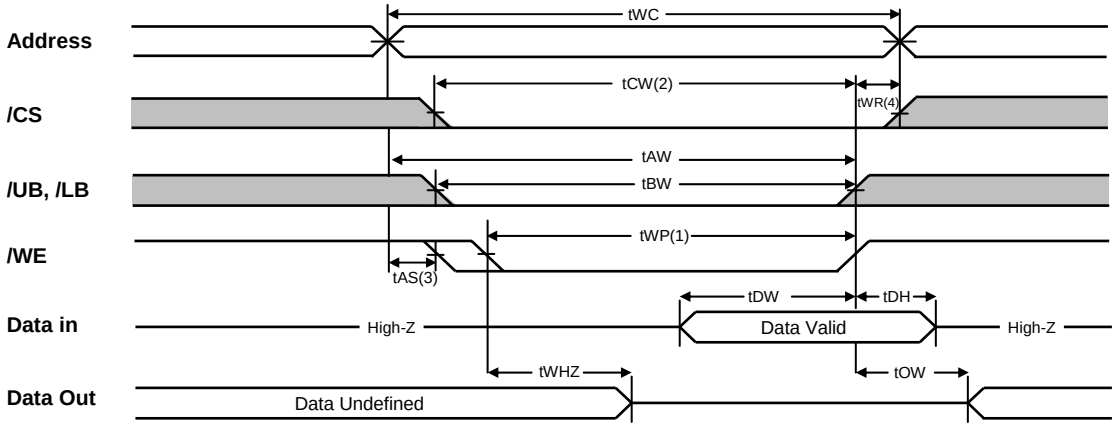


READ CYCLE (2) (/WE=VIH)

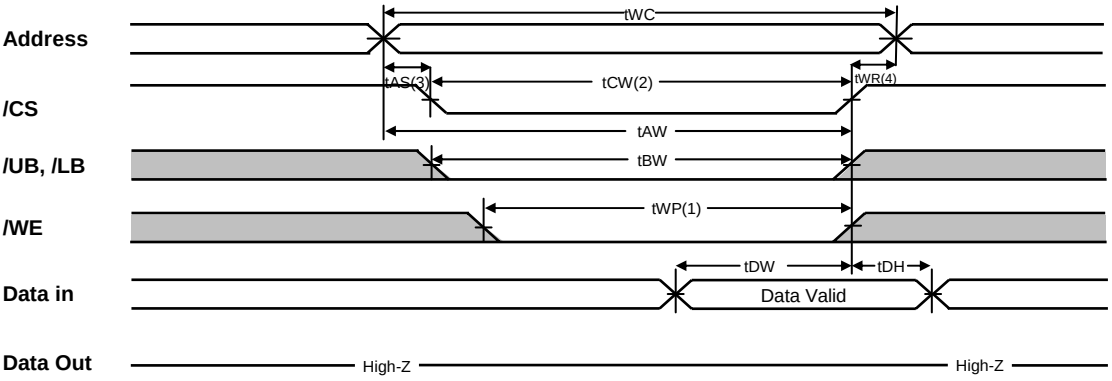


1. tHZ and tOHZ are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, tHZ(Max.) is less than tLZ(Min.) both for a given device and from device to device interconnection.
3. Do not access device with cycle timing shorter than tRC(tWC) for continuous periods > 80us.

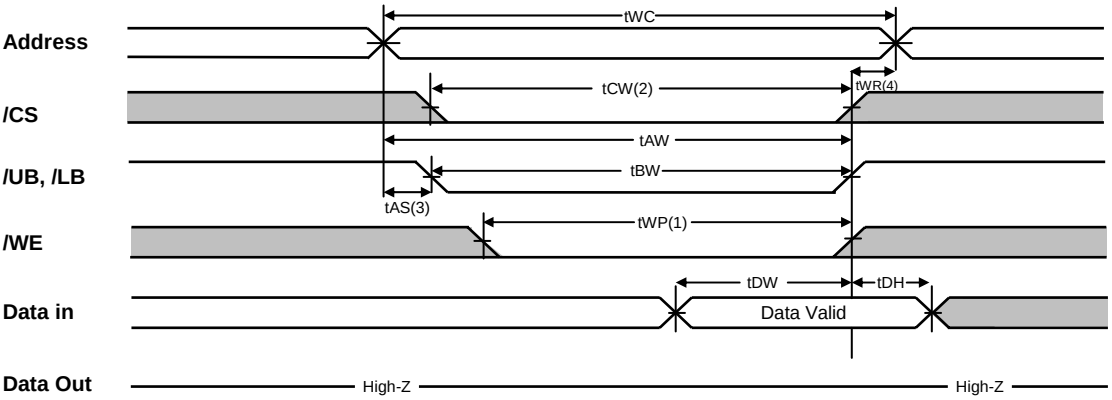
WRITE CYCLE (1) (/WE controlled)



WRITE CYCLE (2) (/CS controlled, /WE=VIH)



WRITE CYCLE (3) (/UB, /LB controlled)

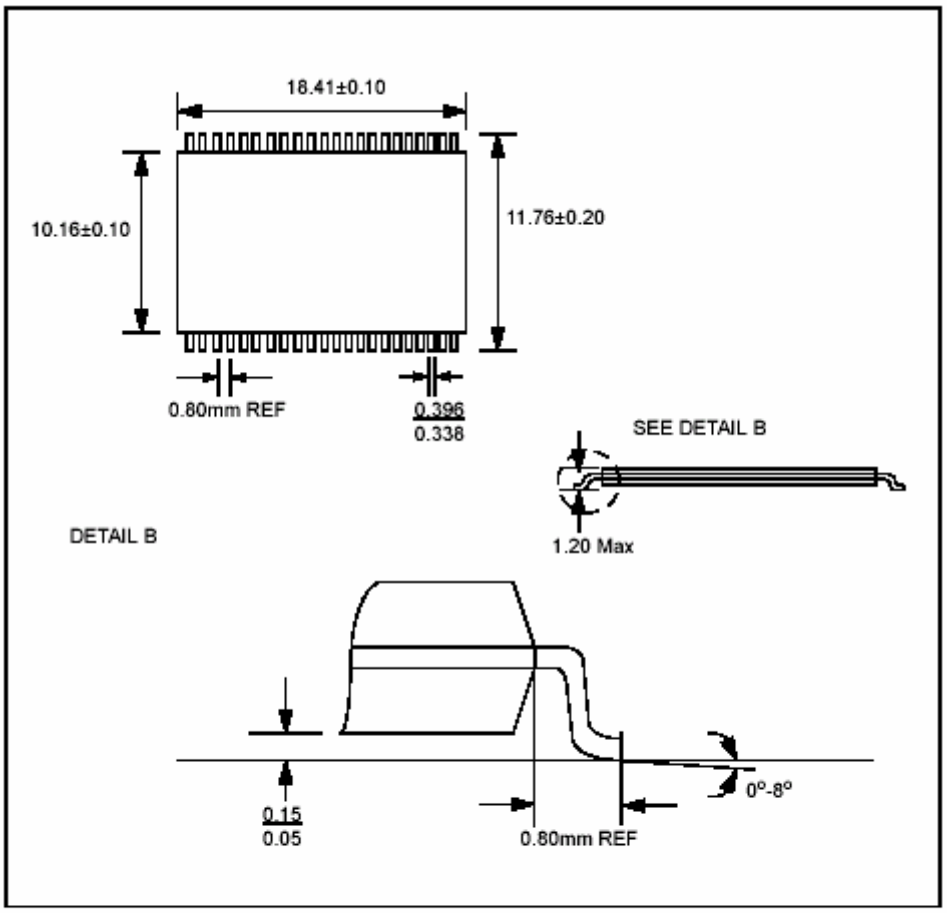


1. A write occurs during the overlap (tWP) of low /CS and /WE. A write begins when /CS goes low and /WE goes low with asserting /UB or /LB for single byte operation or simultaneously asserting /UB and /LB for double byte operation. A write ends at the earliest transition when /CS goes high and WE goes high. The tWP is measured from the beginning of write to the end of write.
2. tCW is measured from the /CS going low to end of write.
3. tAS is measured from the address valid to the beginning of write.
4. tWR is measured from the end of write to the address change. tWR applied in case a write ends as /CS or /WE going high.
5. Do not access device with cycle timing shorter than tRC(tWC) for continuous periods > 80us.

PACKAGE DIMENSION

Unit : millimeters

44 PIN THIN SMALL OUTLINE PACKAGE TYPE II (400F)



Note:
1. All dimensions in inches (Millimeters)
2. Package dimensions exclude molding flash